

International Rectifier

ST1230C..K SERIES

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey-puk

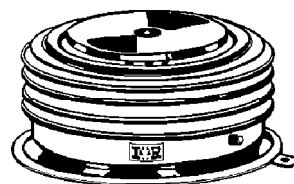
Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST1230C..K	Units
$I_{T(AV)}$	1745	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	3200	A
@ T_{hs}	25	°C
I_{TSM}	@ 50Hz	33500 A
	@ 60Hz	35100 A
I^2t	@ 50Hz	5615 KA ² s
	@ 60Hz	5126 KA ² s
V_{DRM}/V_{RRM}	800 to 1600	V
t_q typical	200	μs
T_J	- 40 to 125	°C

1745A



case style A-24 (K-PUK)



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST1230C..K	08	800	900	100
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

On-state Conduction

Parameter	ST1230C..K	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	1745 (710)	A	180° conduction, half sine wave
	55 (85)	°C	double side (single side) cooled
$I_{T(RMS)}$ Max. RMS on-state current	3200	A	DC @ 25°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	33500		t = 10ms No voltage
	35100		t = 8.3ms reapplied
	28200		t = 10ms 100% V_{RRM}
	29500		t = 8.3ms reapplied
I^2t Maximum I^2t for fusing	5615	KA ² s	t = 10ms No voltage
	5126		t = 8.3ms reapplied
	3971		t = 10ms 100% V_{RRM}
	3625		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	56150	KA ² /s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.93	V	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	1.02		($I > \pi \times I_{T(AV)}$), $T_J = T_J$ max.
r_{t1} Low level value of on-state slope resistance	0.17	mΩ	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ max.
r_{t2} High level value of on-state slope resistance	0.16		($I > \pi \times I_{T(AV)}$), $T_J = T_J$ max.
V_{TM} Max. on-state voltage	1.62	V	$I_{pk} = 4000A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L Typical latching current	1000		



Switching

Parameter	ST1230C..K	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/ μ s	Gate drive 20V, 20 Ω , $t_r \leq 1\mu$ s $T_J = T_J$ max, anode voltage $\leq 80\% V_{DRM}$
t_d Typical delay time	1.9	μ s	Gate current 1A, $di_g/dt = 1A/\mu$ s $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ\text{C}$
t_q Typical turn-off time	200		$I_{TM} = 550A$, $T_J = T_J$ max, $di/dt = 40A/\mu$ s, $V_R = 50V$ $dv/dt = 20V/\mu$ s, Gate 0V 100 Ω , $t_p = 500\mu$ s

Blocking

Parameter	ST1230C..K	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	100	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter		ST1230C..K		Units	Conditions
P _{GM}	Maximum peak gate power	16		W	T _J = T _J max, t _p ≤ 5ms
P _{G(AV)}	Maximum average gate power	3			T _J = T _J max, f = 50Hz, d% = 50
I _{GM}	Max. peak positive gate current	3.0		A	T _J = T _J max, t _p ≤ 5ms
+V _{GM}	Maximum peak positive gate voltage	20		V	T _J = T _J max, t _p ≤ 5ms
-V _{GM}	Maximum peak negative gate voltage	5.0			
I _{GT}	DC gate current required to trigger	TYP.	MAX.	mA	T _J = - 40°C T _J = 25°C T _J = 125°C Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
		200	-		
		100	200		
		50	-		
V _{GT}	DC gate voltage required to trigger	1.4	-	V	T _J = - 40°C T _J = 25°C T _J = 125°C
		1.1	3.0		
		0.9	-		
I _{GD}	DC gate current not to trigger	10		mA	T _J = T _J max Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V _{DRM} anode-to-cathode applied
V _{GD}	DC gate voltage not to trigger	0.25		V	



Thermal and Mechanical Specification

Parameter	ST1230C..K	Units	Conditions
T_J Max. operating temperature range	-40 to 125	°C	
T_{stg} Max. storage temperature range	-40 to 150		
R_{thJ-hs} Max. thermal resistance, junction to heatsink	0.042 0.021	K/W	DC operation single side cooled DC operation double side cooled
R_{thC-hs} Max. thermal resistance, case to heatsink	0.006 0.003	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, $\pm 10\%$	24500 (2500)	N (Kg)	
wt Approximate weight	425	g	
Case style	A-24 (K-PUK)		See Outline Table

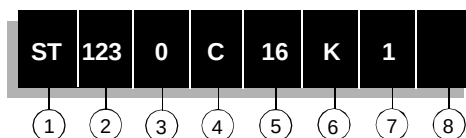
 ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.003	0.003	0.002	0.002	K/W	$T_J = T_J \text{ max.}$
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Ordering Information Table

Device Code



- 1** - Thyristor
- 2** - Essential part number
- 3** - 0 = Converter grade
- 4** - C = Ceramic Puk
- 5** - Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)
- 6** - K = Puk Case A-24 (K-PUK)
- 7** - 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)
1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)
2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)
- 8** - Critical dv/dt: None = 500V/ μ sec (Standard selection)
L = 1000V/ μ sec (Special selection)

Outline Table

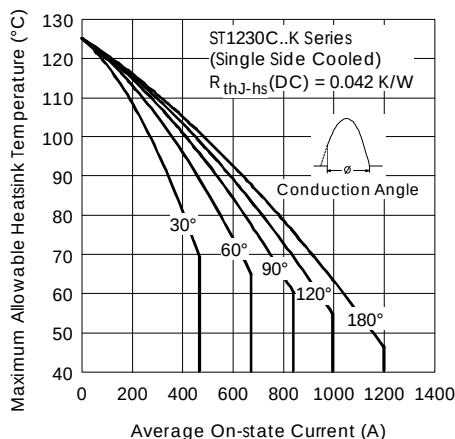
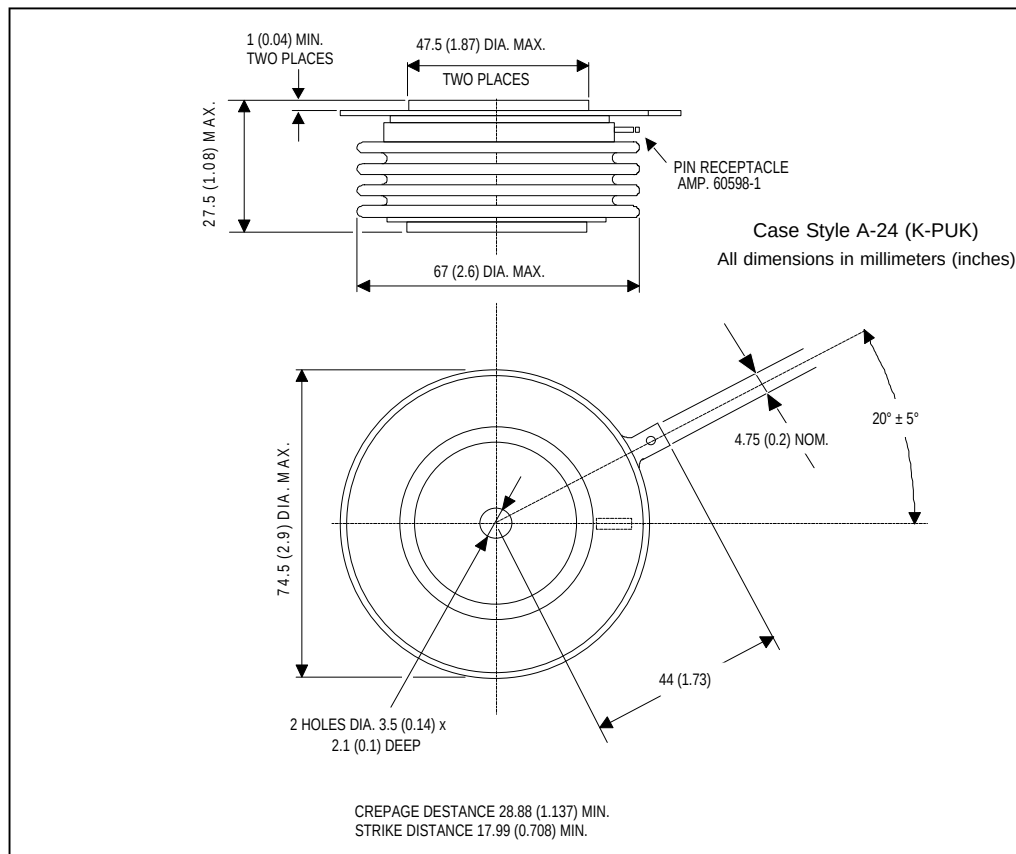


Fig. 1 - Current Ratings Characteristics

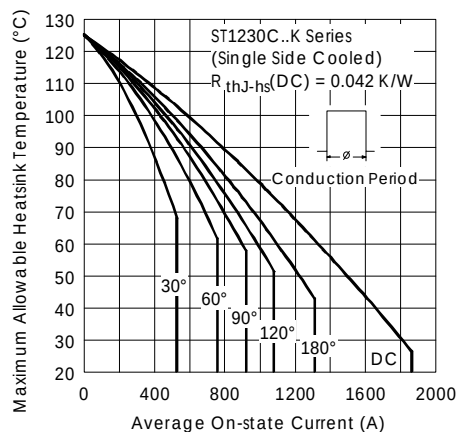


Fig. 2 - Current Ratings Characteristics



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Электрон
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